

TOSHIBA Transistor Silicon PNP Epitaxial Type

2SA2069

High-Speed Switching Applications
DC-DC Converter Applications

- High DC current gain: $h_{FE} = 200$ to 500 ($I_C = -0.15$ A)
- Low collector-emitter saturation voltage: $V_{CE(sat)} = -0.14$ V (max)
- High-speed switching: $t_f = 37$ ns (typ.)

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

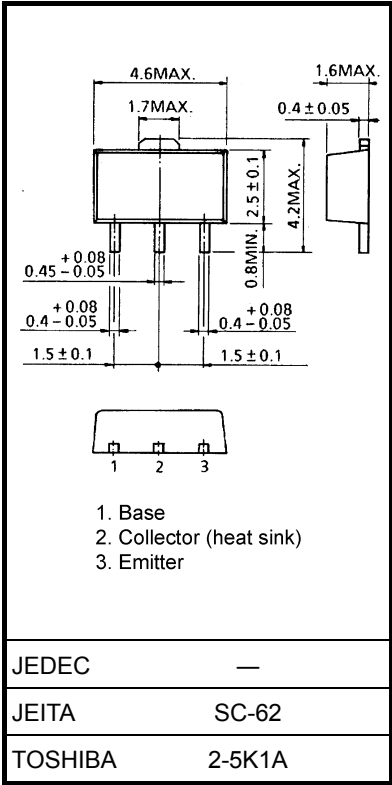
| Characteristics | | Symbol | Rating | Unit |
|-----------------------------|------------|-----------|------------|--------------------|
| Collector-base voltage | | V_{CBO} | -20 | V |
| Collector-emitter voltage | | V_{CEO} | -20 | V |
| Emitter-base voltage | | V_{EBO} | -7 | V |
| Collector current | DC | I_C | -1.5 | A |
| | Pulse | I_{CP} | -2.5 | |
| Base current | | I_B | -150 | mA |
| Collector power dissipation | $t = 10$ s | P_C | 2.0 | W |
| | DC | (Note 1) | 1.0 | |
| Junction temperature | | T_j | 150 | $^{\circ}\text{C}$ |
| Storage temperature range | | T_{stg} | -55 to 150 | $^{\circ}\text{C}$ |

Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



Weight: 0.05 g (typ.)

Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------------|--------------|----------------|--|-----|------|-------|------|
| Collector cut-off current | | I_{CBO} | $V_{CB} = -20\text{ V}, I_E = 0$ | — | — | -100 | nA |
| Emitter cut-off current | | I_{EBO} | $V_{EB} = -7\text{ V}, I_C = 0$ | — | — | -100 | nA |
| Collector-emitter breakdown voltage | | $V_{(BR) CEO}$ | $I_C = -10\text{ mA}, I_B = 0$ | -20 | — | — | V |
| DC current gain | | $h_{FE} (1)$ | $V_{CE} = -2\text{ V}, I_C = -0.15\text{ A}$ | 200 | — | 500 | |
| | | $h_{FE} (2)$ | $V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$ | 125 | — | — | |
| Collector-emitter saturation voltage | | $V_{CE (sat)}$ | $I_C = -0.5\text{ A}, I_B = -17\text{ mA}$ | — | — | -0.14 | V |
| Base-emitter saturation voltage | | $V_{BE (sat)}$ | $I_C = -0.5\text{ A}, I_B = -17\text{ mA}$ | — | — | -1.10 | V |
| Collector output capacitance | | C_{ob} | $V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$ | — | 12 | — | pF |
| Switching time | Rise time | t_r | See Figure 1. $V_{CC} \approx -10\text{ V}, R_L = 20\ \Omega$ $-I_{B1} = I_{B2} = -17\text{ mA}$ | — | 40 | — | ns |
| | Storage time | t_{stg} | | — | 135 | — | |
| | Fall time | t_f | | — | 37 | — | |

Marking

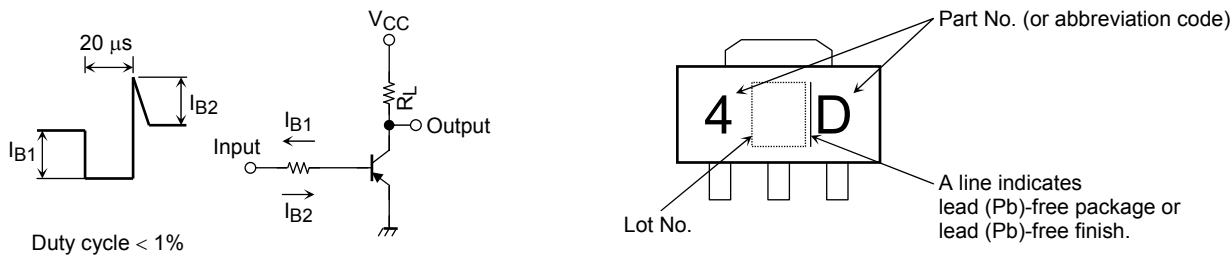
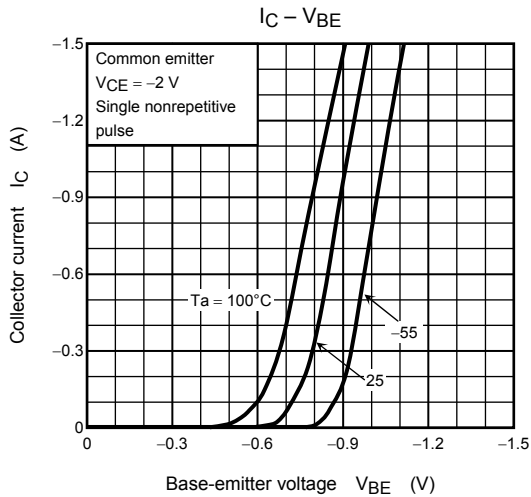
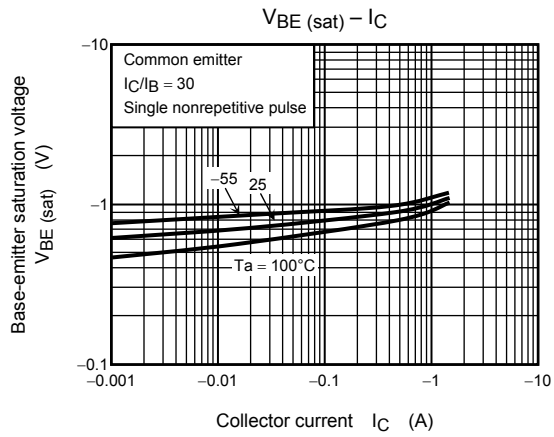
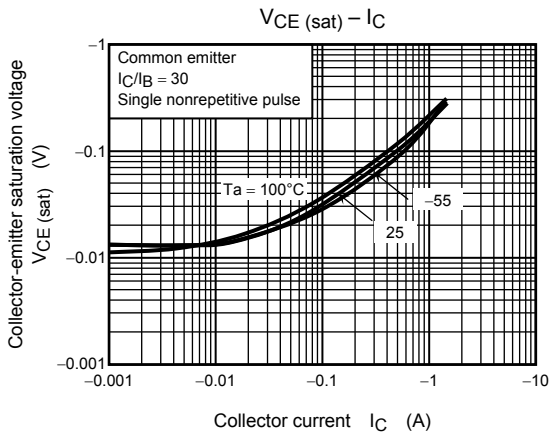
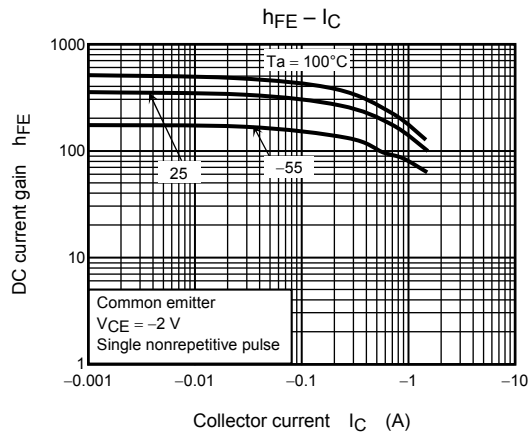
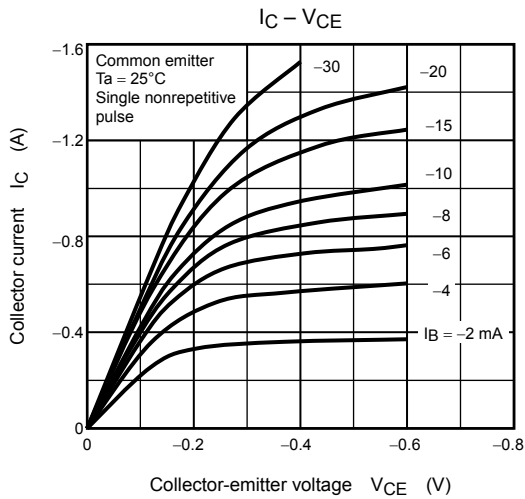
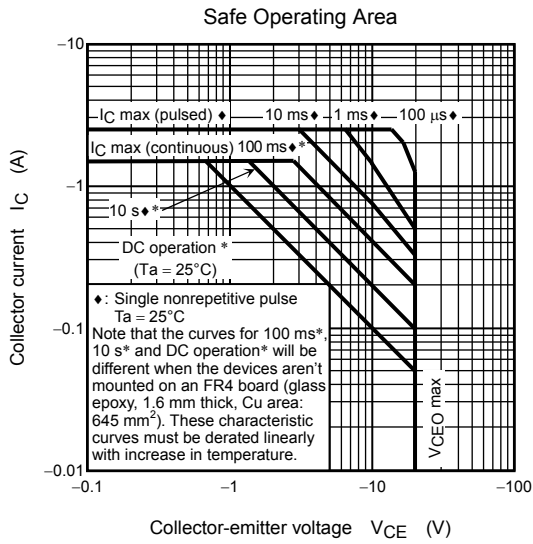
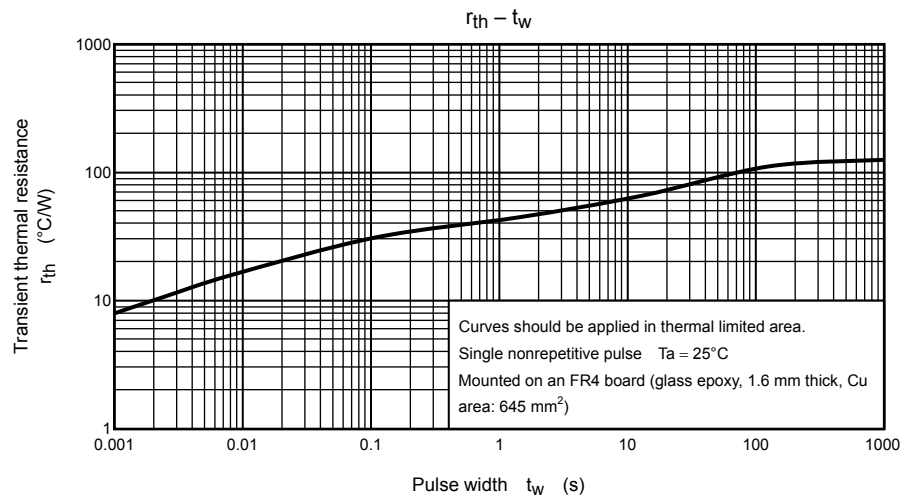


Figure 1 Switching Time Test Circuit & Timing Chart





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